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20-Micron-Thick Si Solar Cells with 20% AM0 Efficiency

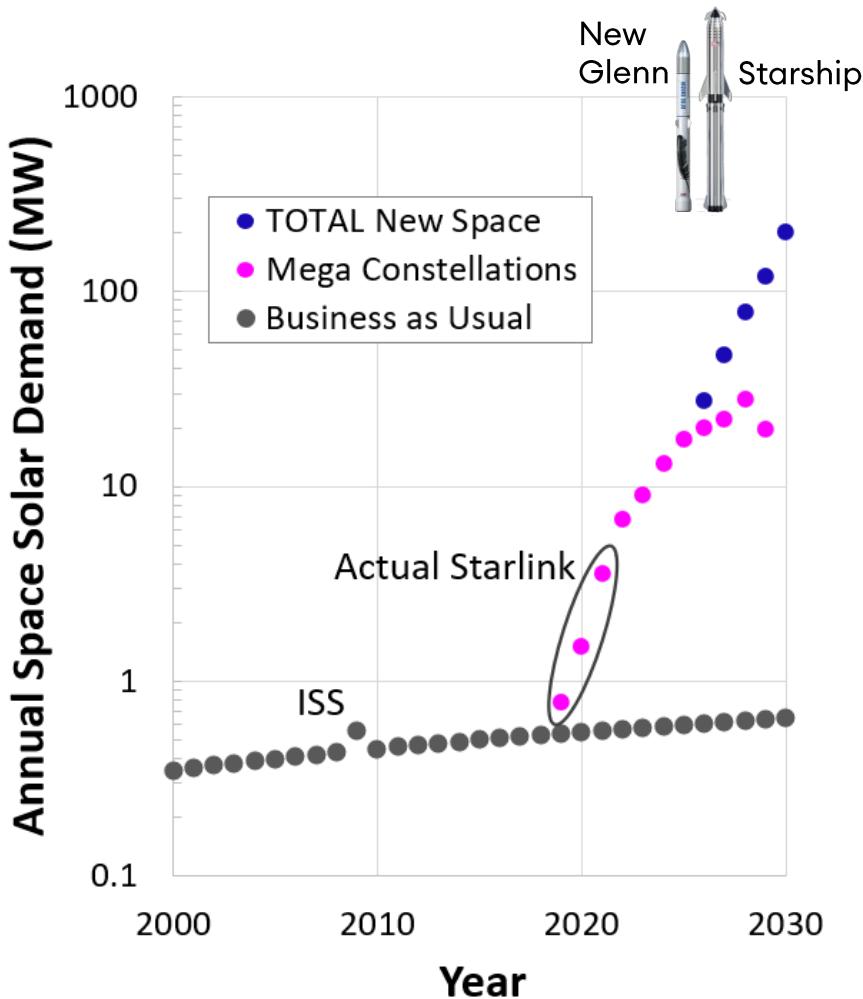
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Motivation and Cell Structure

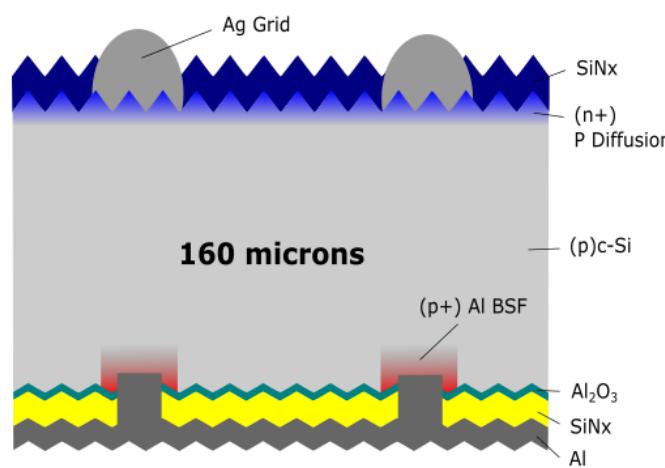
Why Silicon?



What Type of Silicon?

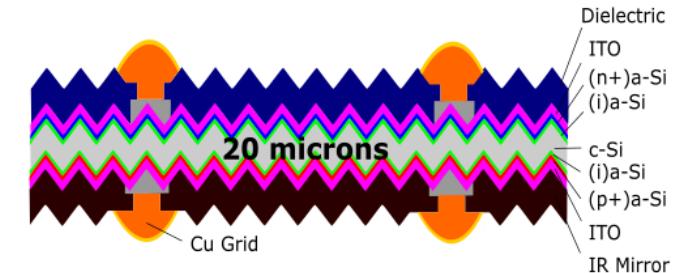
Commercial Cells

- 160-micron-thick Diffused Junction Screen printed Ag and Al
- Degrades fast under radiation
- Rigid



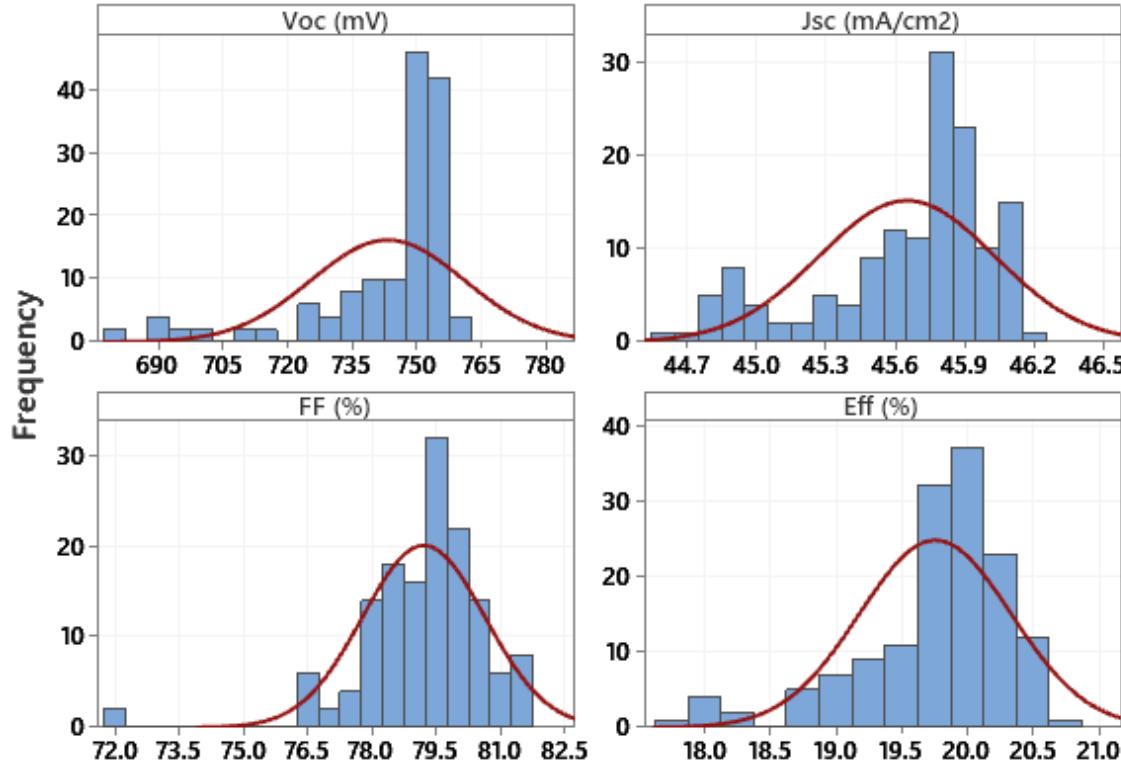
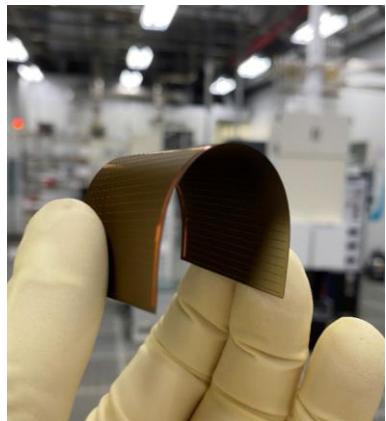
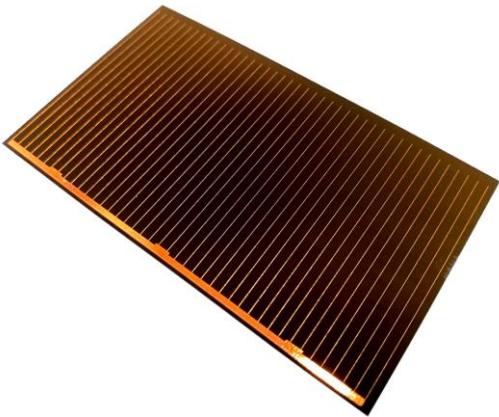
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- 20-micron-thick a-Si/c-Si Heterojunction Electroplated Cu
- Potentially more radiation hard
- Light-weight and flexible



R&D Pilot Production

- 144 solar cells.
- Standard ‘space’ form-factor, 76 x 45 mm² area.
- 20% BOL AM0 efficiency.
- Current drop compensated by voltage increase.
- 0.26 g per cell, 3500 W/kg specific power.
- 10,000 W/kg potential with Si and Cu volume reduction.



Voc (mV)	Mean	743.2
	StDev	17.75
	N	144
Jsc (mA/cm ²)	Mean	45.65
	StDev	0.3799
	N	144
FF (%)	Mean	79.21
	StDev	1.428
	N	144
Eff (%)	Mean	19.76
	StDev	0.5784
	N	144

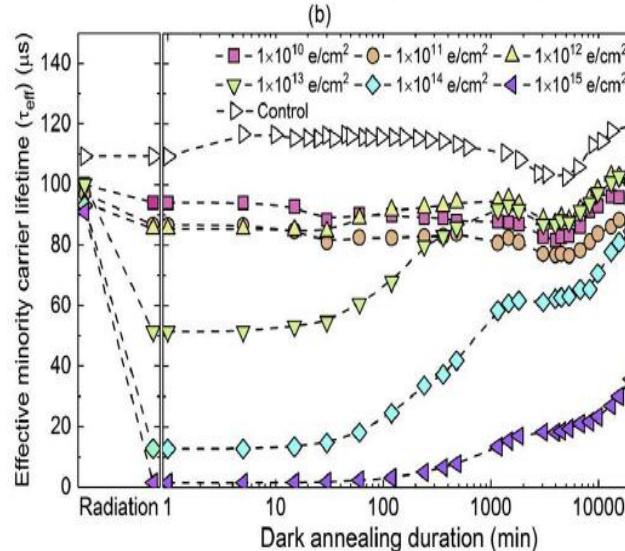
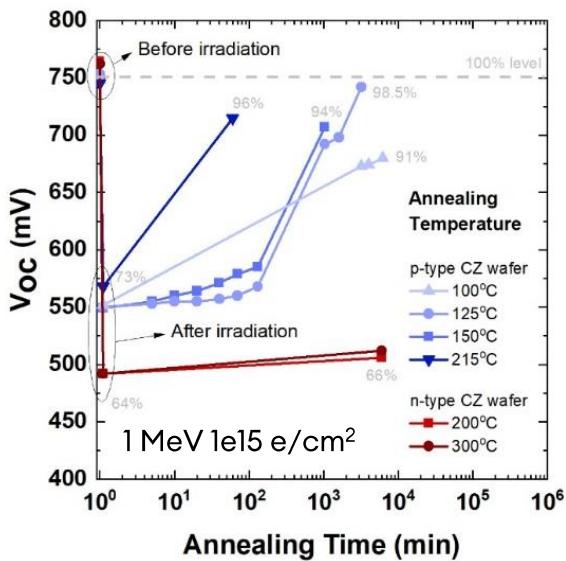
* Efficiency measured in-house using AM1.5 source with 1366 W/m² intensity at 28°C. Current adjusted for AM0 using QE.

Radiation Hardness of Silicon

- Approach: promote defect reaction to (1) dissociate recombination active defects and/or (2) promote the formation of less recombination active defects.

Electron-Induced Defects

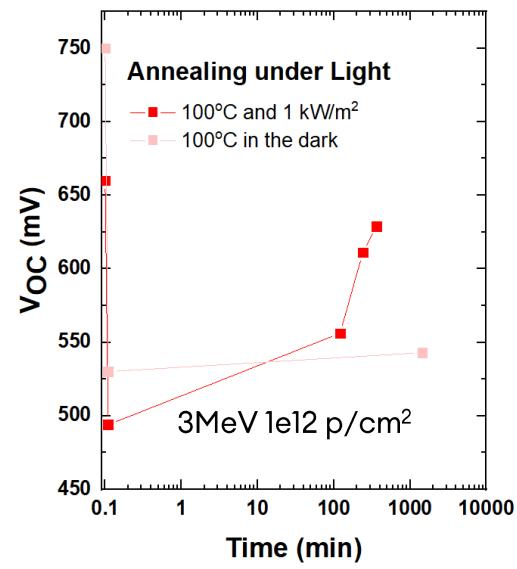
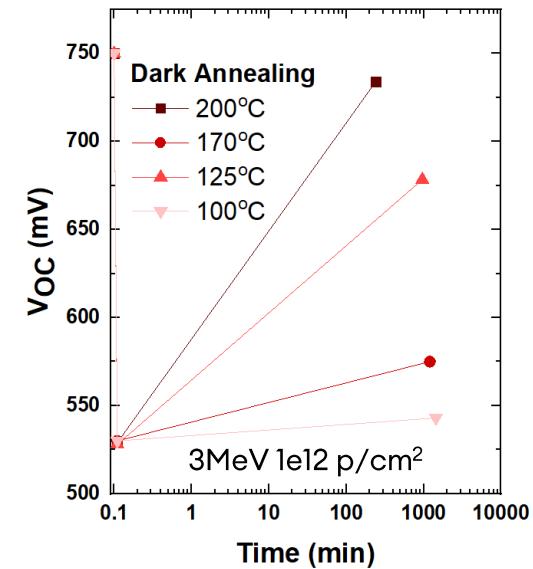
	Thickness (um)	T (°C)	EOL	Factor	Time (min)
Herasimenka ¹	20	100	700/750 mV	BO	5,000
Khan ²	180	150	40/100 us	H	10,000



Proton-Induced Defects

Key Findings:

- 100°C not sufficient to recover proton damage
- Illumination increases recovery rate



¹S. Herasimenka, et al., presented at Space Power Workshop 2019.

²M. U. Khan, et al., Sol. Energy Mater. Sol. Cells 200, 109990 (2019).